

PBSS4041NZ

60 V, 7 A NPN low VCEsat (BISS) transistor Rev. 2 — 8 August 2012

Product data sheet

Product profile 1.

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS4041PZ.

1.2 Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FF}) at high I_C

1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management

1.4 Quick reference data

- High energy efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller required PCB area than for conventional transistors
- Charging circuits
- Power switches (e.g. motors, fans)

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	60	V
I _C	collector current		-	-	7	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	15	А
R _{CEsat}	collector-emitter saturation resistance	$I_C = 6$ A; $I_B = 600$ mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02 ; $T_{amb} = 25$ °C	-	17.5	25	mΩ

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		<u> </u>
2	С	collector		C
3	Е	emitter		в
4	С	collector		
			SOT223 (SC-73)	E sym123

3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PBSS4041NZ	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223		

4. Marking

Table 4. Marking codes	
Type number	Marking code
PBSS4041NZ	PB4041NZ

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	60	V
V _{CEO}	collector-emitter voltage	open base		-	60	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	7	А
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	15	А
I _B	base current			-	1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u>	-	770	mW
			[2]	-	1700	mW
			[3]	-	2600	mW

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Table 5. Limiting values ...continued

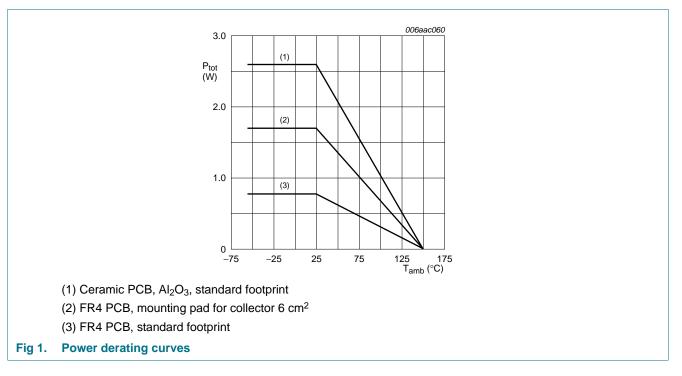
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	150	°C
T _{stg}	storage temperature		-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



6. Thermal characteristics

Table 6.Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient			<u>[1]</u>	-	-	160	K/W
		[2]	-	-	75	K/W	
	amplem		[3]	-	-	50	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	11	K/W

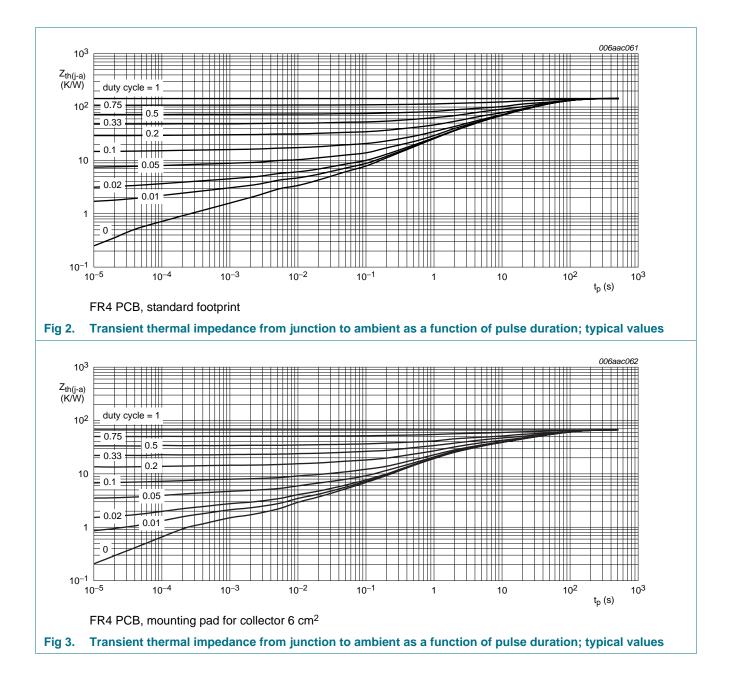
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

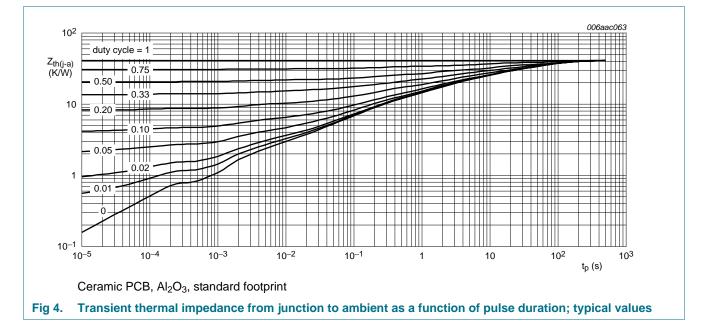
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7. Characteristics

Table 7. Characteristics

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = 60 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$	-	-	100	nA
current	current	$V_{CB} = 60 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{j} = 150 \text{ °C}$	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = 48 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = 5 V; I_C = 0 A; T_{amb} = 25 °C	-	-	100	nA
h _{FE} DC current gain	DC current gain	$ \begin{array}{l} V_{CE} = 2 \ V; \ I_{C} = 500 \ mA; \ pulsed; \\ t_{p} \leq 300 \ \mus; \ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^{\circ}C \end{array} $	300	500	-	
		$\label{eq:VCE} \begin{array}{l} V_{CE} = 2 \ V; \ I_{C} = 1 \ A; \ pulsed; \ t_{p} \leq 300 \ \mu s; \\ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^{\circ}C \end{array}$	300	500	-	
		$\label{eq:VCE} \begin{array}{l} V_{CE} = 2 \ V; \ I_C = 2 \ A; \ pulsed; \ t_p \leq 300 \ \mu s; \\ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^\circ C \end{array}$	300	500	-	
		$\label{eq:VCE} \begin{array}{l} V_{CE} = 2 \ \text{V;} \ \text{I}_{C} = 4 \ \text{A; pulsed;} \ t_{p} \leq 300 \ \text{\mu s;} \\ \delta \leq 0.02 \ \text{;} \ \text{T}_{amb} = 25 \ ^{\circ}\text{C} \end{array}$	250	400	-	
		$\label{eq:Vce} \begin{array}{l} V_{CE} = 2 \ V; \ I_C = 6 \ A; \ pulsed; \ t_p \leq 300 \ \mu s; \\ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^\circ C \end{array}$	100	200	-	
		$\label{eq:Vce} \begin{array}{l} V_{CE} = 2 \ V; \ I_C = 7 \ A; \ pulsed; \ t_p \leq 300 \ \mu s; \\ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^\circ C \end{array}$	50	100	-	

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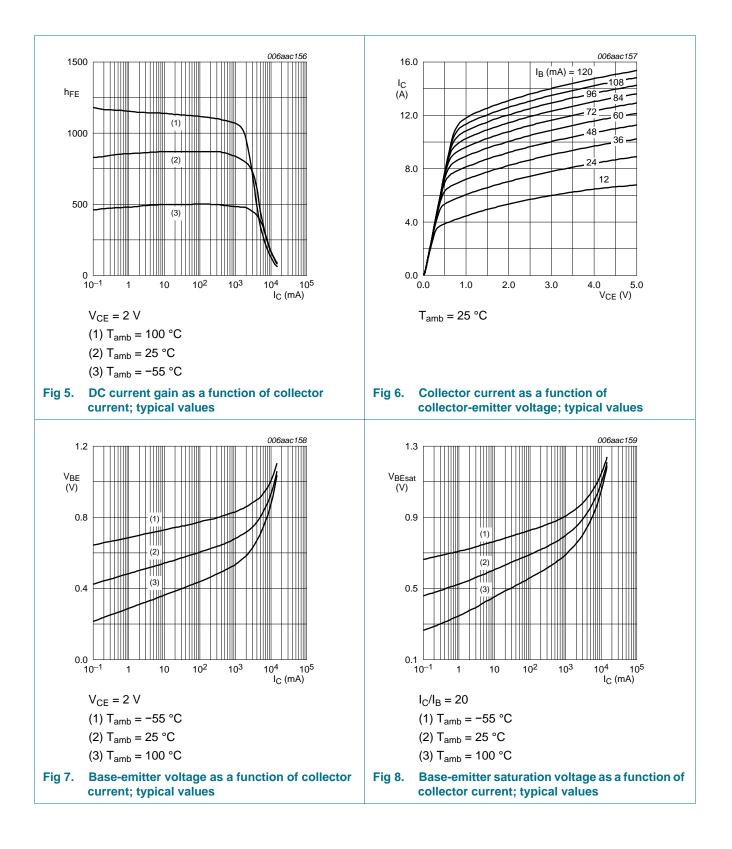
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = 1 \text{ A}; I_{B} = 50 \text{ mA}; \text{ pulsed};$ $t_{p} \leq 300 \mu\text{s}; \delta \leq 0.02 ; T_{amb} = 25 ^{\circ}\text{C}$	-	25	35	mV
		I_{C} = 1 A; I_{B} = 10 mA; pulsed; $t_{p} \le 300 \ \mu$ s; $\delta \le 0.02$; T_{amb} = 25 °C	-	43	60	mV
		I_{C} = 2 A; I_{B} = 40 mA; pulsed; $t_{p} \le 300 \mu\text{s}; \delta \le 0.02$; T_{amb} = 25 °C	-	53	75	mV
		$ I_C = 4 \text{ A}; I_B = 200 \text{ mA}; \text{ pulsed}; $	-	78	110	mV
		$I_{C} = 4 \text{ A}; I_{B} = 40 \text{ mA}; \text{ pulsed};$ $t_{p} \le 300 \mu\text{s}; \delta \le 0.02 \text{ ; } T_{amb} = 25 ^{\circ}\text{C}$	-	115	160	mV
		$ I_C = 7 \text{ A}; I_B = 350 \text{ mA}; \text{ pulsed}; $	-	130	195	mV
R _{CEsat}	collector-emitter saturation resistance	$ I_C = 6 \text{ A}; I_B = 600 \text{ mA}; \text{ pulsed}; $	-	17.5	25	mΩ
V _{BEsat}	V _{BEsat} base-emitter saturation voltage	I_{C} = 1 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; $\delta \le 0.02$; T_{amb} = 25 °C	-	0.83	0.9	V
		$ I_C = 4 \text{ A}; I_B = 400 \text{ mA}; \text{ pulsed}; $	-	0.98	1.05	V
V _{BEon}	base-emitter turn-on voltage	$\label{eq:Vce} \begin{array}{l} V_{CE} = 2 \ \mbox{V;} \ \mbox{I}_{C} = 2 \ \mbox{A;} \ \mbox{pulsed;} \ \mbox{t}_{p} \leq 300 \ \mbox{\mus;} \\ \delta \leq 0.02 \ \ \ \mbox{T}_{amb} = 25 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $	-	0.72	0.85	V
t _d	delay time	V_{CC} = 12.5 V; I _C = 1 A; I _{Bon} = 0.05 A;	-	55	-	ns
t _r	rise time	I _{Boff} = -0.05 A; T _{amb} = 25 °C	-	55	-	ns
t _{on}	turn-on time		-	110	-	ns
t _s	storage time		-	1220	-	ns
t _f	fall time		-	230	-	ns
t _{off}	turn-off time		-	1450	-	ns
f _T	transition frequency	V_{CE} = 10 V; I _C = 100 mA; f = 100 MHz; T _{amb} = 25 °C	-	105	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; T _{amb} = 25 °C	-	50	-	pF

Table 7. Characteristics ...continued

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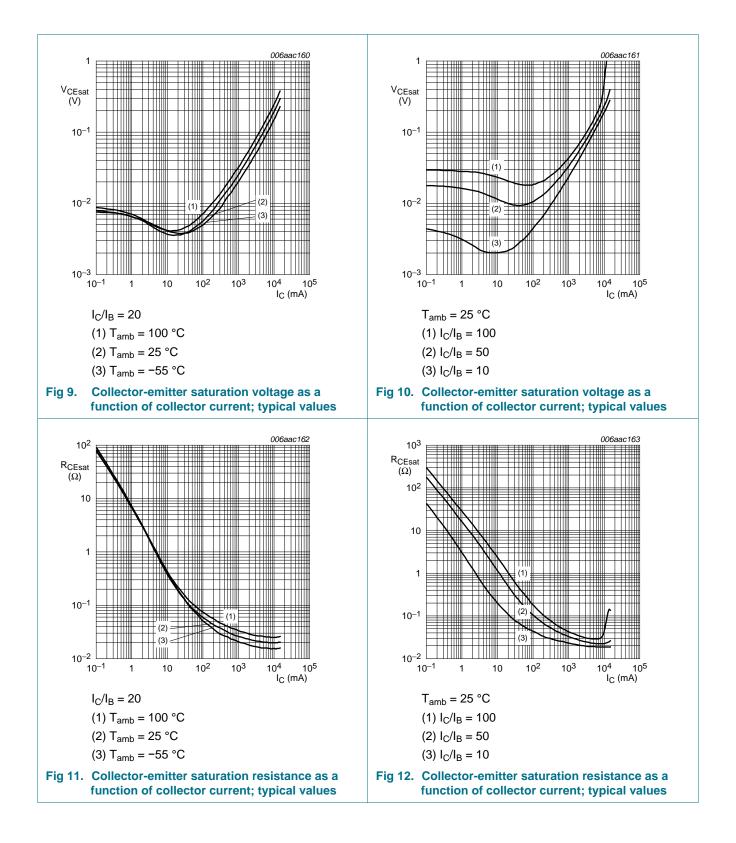
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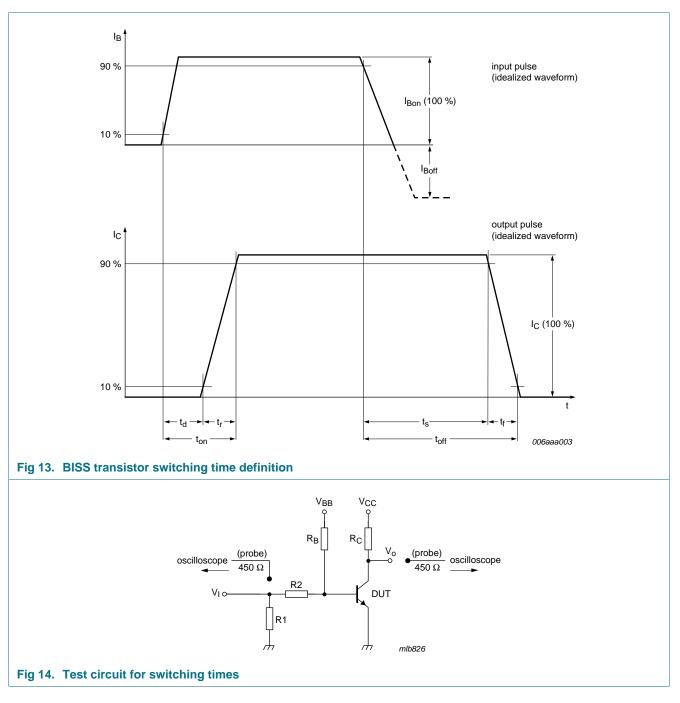
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8. Test information



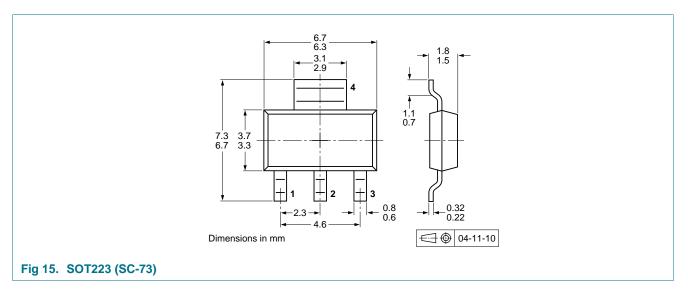
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard*Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

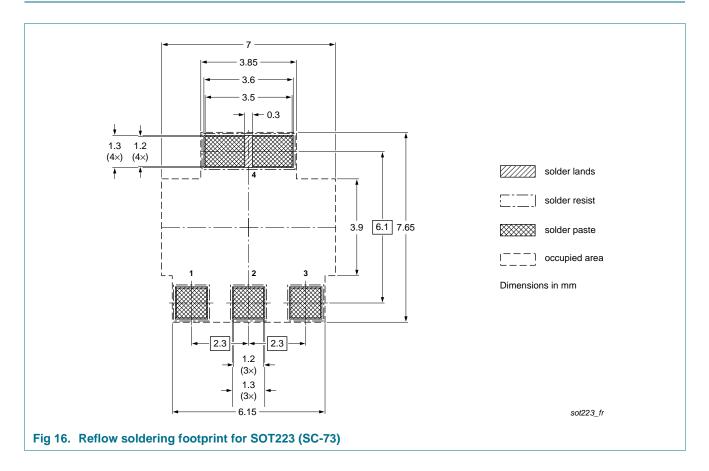
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9. Package outline

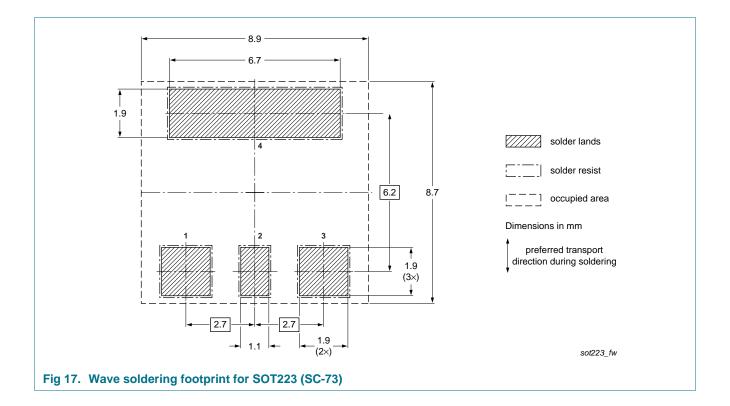


10. Soldering



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11. Revision history

Table 8. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4041NZ v.2	20120808	Product data sheet	-	PBSS4041NZ v.1
Modifications:		stics": V _{CEsat} corrected		
PBSS4041NZ v.1	20100331	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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